



### Photocell (CdS) Output Optocoupler

The NSL-32 is an optocoupler (optoisolator) with an LED input optically coupled to a CdS Light Dependent Resistor (LDR) photocell. It is an optoelectronic component that interconnects two separate electrical circuits by means of a light sensitive optical interface. The photoresistor resistance increases when the LED current is "off" and decreases when the LED current is "on".

## **Applications**

Industrial Audio Compressors Electrical Noise Filter

## **Features**

| Compact Moisture Resistant Packa | ge |
|----------------------------------|----|
| Low LED Current                  |    |
| Passive Resistance Output        |    |
| Low Distortion                   |    |
| Suitable for AC or DC            |    |







### **Absolute Maximum Ratings**

| Parameter                      | Symbol           | Min | Max  | Unit |
|--------------------------------|------------------|-----|------|------|
| Isolation Voltage              | V <sub>B</sub>   | -   | 2000 | V    |
| Power Dissipation <sup>1</sup> | -                | -   | 50   | mW   |
| Operating Temperature          | T <sub>op</sub>  | -40 | +75  | °C   |
| Storage Temperature            | T <sub>stg</sub> | -40 | +75  | °C   |

<sup>1</sup>Derate linearly to 0 at 75°C

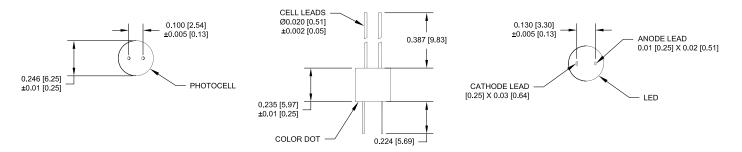
## Typical Electro-Optical Specifications at $T_A = 23 \text{ °C}$

| Parameter              | Test Conditions  | Symbol           | Min | Тур | Max | Unit   |
|------------------------|--|------------------|-----|-----|-----|--------|
| LED                    |  |                  |     |     |     |        |
| Forward Current        | -  | I <sub>F</sub>   | -   | -   | 40  | mA     |
| Forward Voltage        | I <sub>r</sub> =16mA   | $V_{\rm F}$      | -   | -   | 2.5 | V      |
| Reverse Current        | V <sub>R</sub> =4V   | I <sub>R</sub>   | -   | -   | 3   | μΑ     |
| CELL                   |  |                  |     |     |     |        |
| Max. Cell Voltage      | Peak AC or DC  | V <sub>MAX</sub> | -   | -   | 60  | V      |
| COUPLED                |  |                  |     |     |     |        |
| On Resistance          | l,=16mA  | R <sub>on</sub>  | -   | 160 | 200 | Ω      |
| Off Resistance         | 10 sec after $I_r$ =0 mA, 5VDC on cell   | $R_{off}$        | 500 | -   | -   | ΚΩ     |
| Rise Time <sup>2</sup> | Time for the dark to light change in conductance to reach 63% of its final value | T <sub>R</sub>   | -   | 55  | -   | msec   |
| Decay Time             | Time to reach 100KΩ after removal of If=16mA                                     | T <sub>D</sub>   | -   | 80  | -   | msec   |
| Cell Temp. Coefficient | l <sub>f</sub> => 5mA  | α                | -   | 0.7 | -   | % / °C |

<sup>2</sup> The Rise Time, TR, is the time required for the dark to light change in conductance to reach 63% of its final value.

### **Mechanical Specifications**

Units are in inches [mm]



Soldering Conditions:  $260^{\circ}C 1/16$  inch away from case for 3 seconds max.





#### **Care and handling instructions**

Your optoelectronic components are packaged and shipped in opaque, padded containers to avoid ambient light exposure and damage due to shock from dropping or jarring.

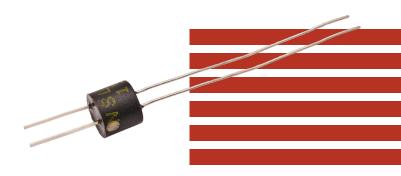
Care must be taken to avoid exposure to high ambient light levels, particularly from tungsten sources or sunlight.

- These components can be rendered inoperable if dropped or sharply jarred. The wire bonds are delicate and can become separated from the bonding pads when the component is dropped or otherwise receives a sharp physical blow.
- Most windows on photodiodes are either silicon or quartz. They should be cleaned with isopropyl alcohol and a soft (optical grade) pad.
- Photodiode exposure to extreme high or low storage temperatures can affect the subsequent performance. Maintain a non-condensing environment for optimum performance and lifetime.
- All devices are considered ESD sensitive. The photodiodes are shipped in ESD protective packaging. When unpacking and using these products, anti-ESD precautions should be observed.
- Photodiode packages and/or operation may be impaired if exposed to CHLOROETHENE, THINNER, ACETONE, TRICHLOROETHYLENE or any harsh chemicals.

#### **Legal Disclaimer**

Information in this data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.

- Optoelectronic components in plastic packages should be given special care. Clear plastic packages are more sensitive to environmental stress than those of black plastic. Storing devices in high humidity can present problems when soldering. Since the rapid heating during soldering stresses the wire bonds and can cause wire to bonding pad separation, it is recommended that devices in plastic packages to be baked for 24 hours at 85°C.
- The leads on the photodiode SHOULD NOT BE FORMED. If your application requires lead spacing modification, please contact Advanced Photonix Applications group at Techsupport@advancedphotonix.com before forming a product's leads. Product warranties could be voided.
- Most devices are provided with wire or pin leads for installation in circuit boards or sockets. Observe the soldering temperatures and conditions specified below:
  - Soldering Iron: Soldering 30 W or less
  - Temperature at tip of iron 300°C or lower.
  - Dip Soldering: Bath Temperature: 260±5°C.
  - Immersion Time: within 5 Sec.
  - Soldering Time: within 3 Sec.
  - Vapor Phase Soldering, Reflow Soldering: DO NOT USE



# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Advanced Photonix: <u>NSL-32</u>